

ABSTRACT

A method for pseudo-planarization of an electromechanical device and for forming a durable metal contact on the electromechanical device and devices formed by the method are presented. The method comprises acts of depositing various layers forming a semiconductor device. Two principal aspects of the method include the formation of a planarized dielectric/conductor layer on a substrate and the formation of an electrode in an armature of a microelectromechanical switch, with the electrode formed such that it interlocks a structural layer of the armature to ensure it remains fixed to the armature over a large number of cycles.